BEGe project: chronology/crystal pulling/plans

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Goal of deplGe BEGe projects

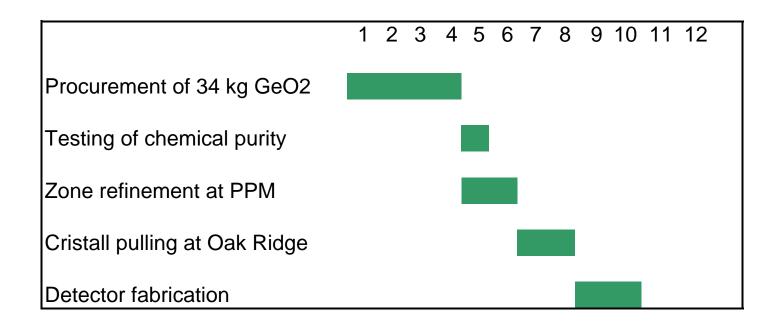
- Show that working BEGe detectors can be produced based on material supply chain (dep/enrGe from ECP; reduction and purification to 6N at PPM; crystal pulling at Oak Ridge; diode fabrication at Olen)
- Test production scheme to maximize detector yield from 37.5 kg enrGe using 20 kg of depGe

project distribution

	prototype	depl. Ge	purification	crystal pulling	detector fabr.	testing
Tuebingen		x		X	(x)	x
Dresden			x			x
Zuerich				X	X	Х
INFN	x			X	X	x
IRMM	x				X	x
MPIK	х			(x)		X

- procurement support by INR
- zone refinement support by MPI Munich

Schedule as of early 2009



Chronology

Jan 28 09: order of 34 kg dep-Ge-oxide by Tuebingen

Apr 6/7 09: Oak Ridge/Meriden – C.Cattadori, A. Garfagnini, St.S.

Apr 30 09: arrival of dep-Ge in Tuebingen

May 5 09: ICPMS results from LNGS

May 12 09: start of reduction and purification at PPM

Jun 22 09: zone refined bars arrived at MPIK (21.4 kg / 91% yield)

Jul 8 09: 21.4 kg material arrived at Oak Ridge as 'temporary

imported goods'

Jul 17 09: zone refinement completed; cutting each bar in 4 slices

Aug 4 09: 1st crystal pulled (#4 piece) Aug 27 09: 2nd crystal pulled (#3 piece)

Sep 30 09: re-growth of #3

Plan:

Until 30. Oct.: #2,#1, re-growth of #4 (tbd)

Nov: meeting at Oak Ridge to discuss selection of slices

shipment of dep-Ge to MPIK => Olen

Dec: start of detector production

Jan/Feb '10: first BEGe from depl-Ge available

Results from crystal growth

4 piece (tail end) - Aug 4:

- top 20% of the ingot is p-type with and net impurity level <1E10, which however is too pure for BEGe's
- residual 80% is n-type
- acceptor impurity is probable Al; donor impurity probable Phosphor;
- ingot was pulled with In-doping for compensation;
- amount of In doping was chosen based on a precursor experiment done by Canberra using their regular material and cutting the zone refined bars in 4 slices (instead of their usual 3 slices).
- crystal can be regrown with and increased In doping with a good chance to achieve BEGe detector quality;
- Milestone: PPM material (after zone refinement at Oak Ridge) suitable for BEGe detector production

#3 piece – Aug 27:

- Net impurity (p-type) level 4E10 too high for BEGe's
- Al contamination in process identified and removed
- Regrowing Sep 30 results: Oct. 2

Preparing the acceptance testing of depleted BEGe's

- 4-5 detectors, above ground at LNGS, Struck FADC from HD
- HV curve, energy resolution, peak tails, active volume and dead layer measurements (241-Am and 60-Co), full PSD performance test with 228-Th
- stability measurement? near electrode sensitivity loss test?
- establish common PSD analysis procedure

People: Dusan, Assunta, Matteo, Alberto, Enrico,

Operation in LAr

N.B: Detector technology same as p-type semi-coax detector

- dismount BEGe crystal from cryostat (80 mm, 70 mm?)
- test in GDL test stands/LArGe
- Optimized FE electronics for BEGe: CSA77 with separate JFET, PZ0, commercial CMOS, other?
- Time slot: Nov/Dec?

